

TO-263

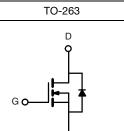
Top View

www.vishay.com

Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.030				
$R_{DS(on)}$ (Ω) at $V_{GS} = 6 \text{ V}$	0.034				
I _D (A)	40				
Configuration	Single				
Package	TO-263				



N-Channel MOSFET

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ABSOLUTE MAXIMUM RATING	S ($T_C = 25$ °C, unless	s otherwise noted	d)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C	ı	40	
Continuous Drain Current	T _C = 125 °C	l _D	22	
Continuous Source Current (Diode Conducti	on) ^a	I _S	60	Α
Pulsed Drain Current b		I _{DM}	155	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	40	
Single Pulse Avalanche Energy	L=U.I IIIH	E _{AS}	80	mJ
Mariana Barra Biratastian b	T _C = 25 °C	Б	107	W
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	35	VV
Operating Junction and Storage Temperatur	T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)		R_{thJC}	1.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		100	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	250	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.023	0.030	Ω	
Due in Course On Chata Basistana 2		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.054		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.067		
		V _{GS} = 6 V	I _D = 10 A	-	0.025	0.034		
Forward Transconductancea	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	52	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	2676	3345	pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	285	355		
Reverse Transfer Capacitance	C _{rss}	1		-	95	120		
Total Gate Charge ^c	Qg			-	41	62		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 40 \text{ A}$	-	11	-	nC	
Gate-Drain Charge ^c	Q_{gd}	1		-	11	-		
Gate Resistance	Rg	f = 1 MHz		0.7	1.3	2.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 50 \text{ V}, R_L = 1.25 \Omega$ $I_D \cong 40 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	12	18		
Rise Time ^c	t _r			-	5	8	1	
Turn-Off Delay Time ^c	t _{d(off)}			-	23	35	ns -	
Fall Time ^c	t _f			-	5	8		
Source-Drain Diode Ratings and Chara	acteristics b							
Pulsed Current ^a	I _{SM}			-	-	155	Α	
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		-	0.85	1.5	V	
							•	

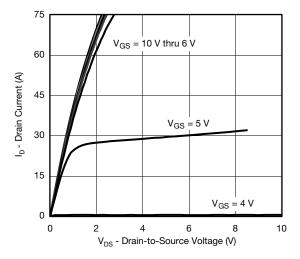
Notes

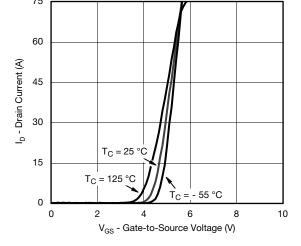
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



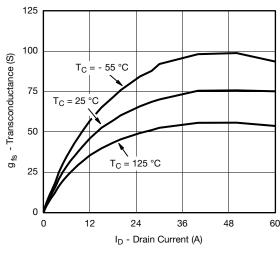
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

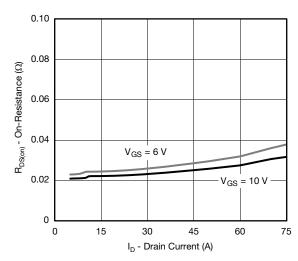




Output Characteristics

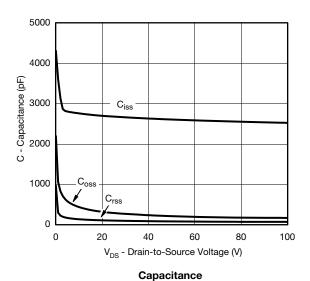


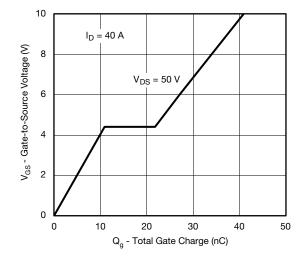




Transconductance

On-Resistance vs. Drain Current

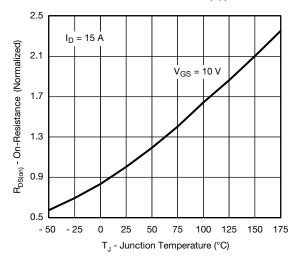




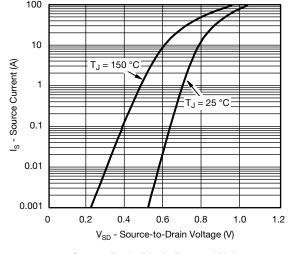
Gate Charge



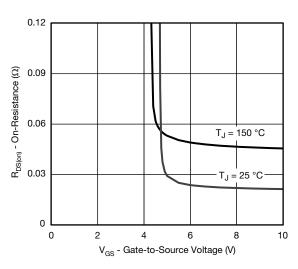
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



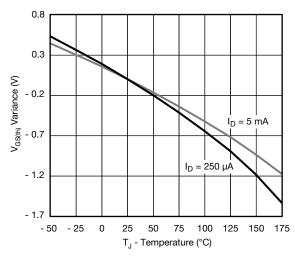
On-Resistance vs. Junction Temperature



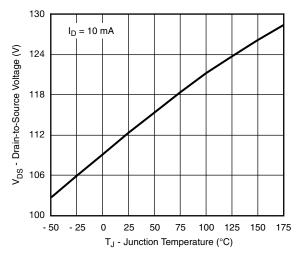
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

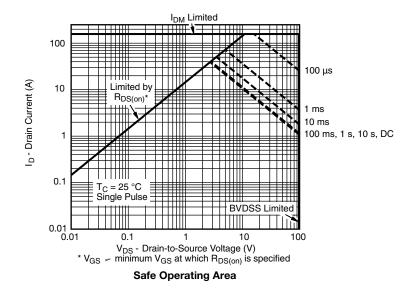


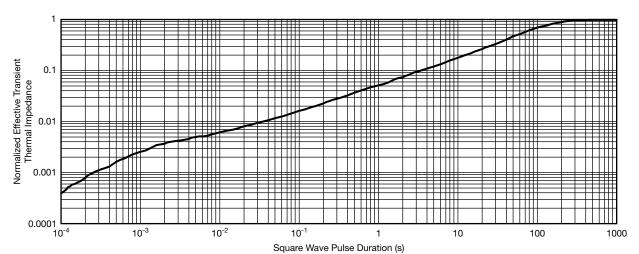
Drain Source Breakdown vs. Junction Temperature

Document Number: 64716



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

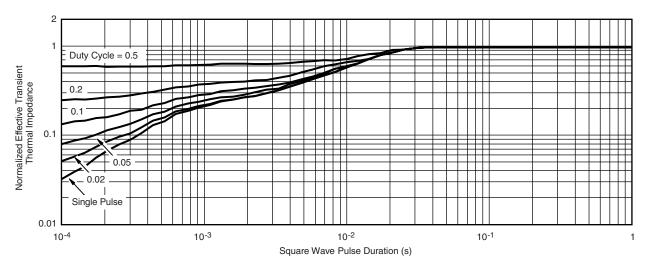




Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?64716.



www.vishay.com

Vishay Siliconix

REVISION HISTORY a				
REVISION	DATE	DESCRIPTION OF CHANGE		
D	04-Aug-15	Revised R _g minimum limit		

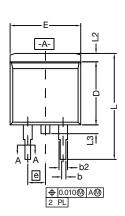
Note

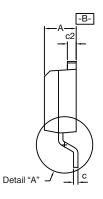
a. As of April 2014

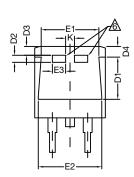




TO-263 (D²PAK): 3-LEAD

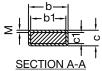








DETAIL A (ROTATED 90°)



1			1
≥⊹	<i>7777777</i>	붓	
ı	WHITTEN S	1	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

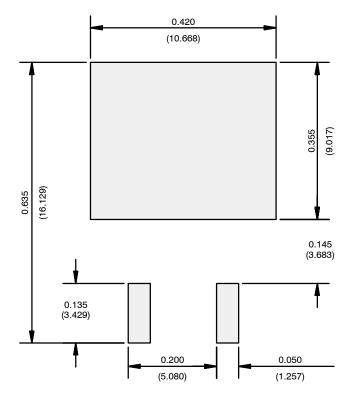
		INCHES		MILLIMETERS	
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045 0.055		1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54	BSC
	K	0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)